

### General Description

The IRFR220N is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The IRFR220N meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

### Product Summary

BVDSS	RDSON	ID
200V	0.21Ω	9A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

### TO-252 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	200	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3.13	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.8	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	36	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	320	mJ
$I_{AS}$	Avalanche Current	9	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>3</sup>	83	W
$P_D@T_C=100^\circ C$	Total Power Dissipation <sup>3</sup>	47	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	30	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	1.6	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	200	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.25	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.5A	---	0.21	0.25	Ω
		V <sub>GS</sub> =6.0V, I <sub>D</sub> =3.6A	---	0.26	0.29	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.8	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.63	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =200V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =160V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =30V, I <sub>D</sub> =4.5A	---	0.21	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2	4	Ω
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =160V, V <sub>GS</sub> =10V, I <sub>D</sub> =9A	---	11.8	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.36	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.98	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =100V, V <sub>GS</sub> =10V, R <sub>G</sub> =10Ω, I <sub>D</sub> =9A, R <sub>L</sub> =10Ω	---	10.33	---	ns
T <sub>r</sub>	Rise Time		---	10.7	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	29.1	---	
T <sub>f</sub>	Fall Time		---	11.1	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	509	---	pF
C <sub>oss</sub>	Output Capacitance		---	51.2	---	
C <sub>riss</sub>	Reverse Transfer Capacitance		---	3.2	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =5A	---	320	---	mJ

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	9	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	36	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =5A, T <sub>J</sub> =25°C	---	---	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =5A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	201	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	663	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=5A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

Typical Characteristics

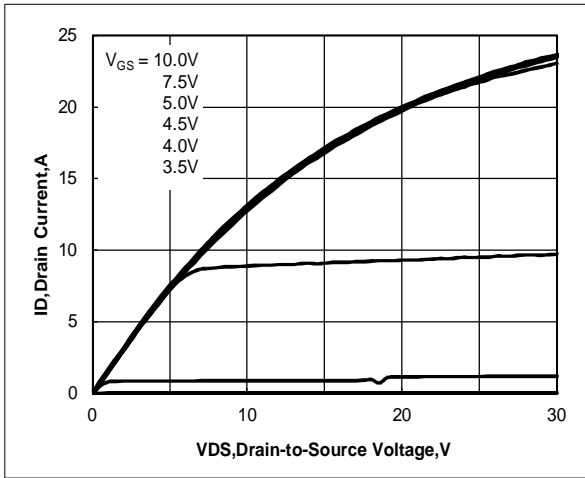


Figure 1. Output Characteristics

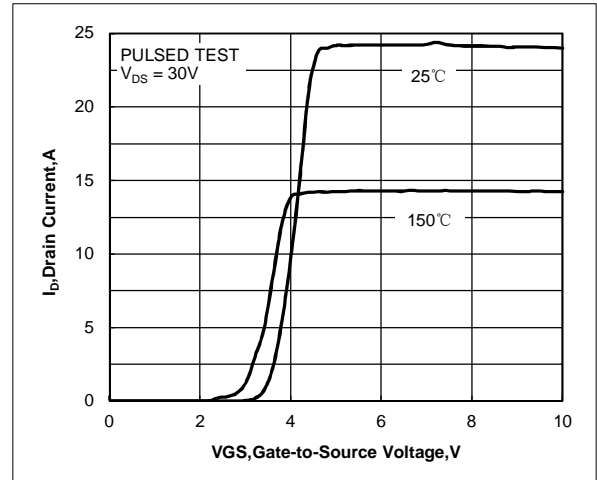


Figure 2. Transfer Characteristics

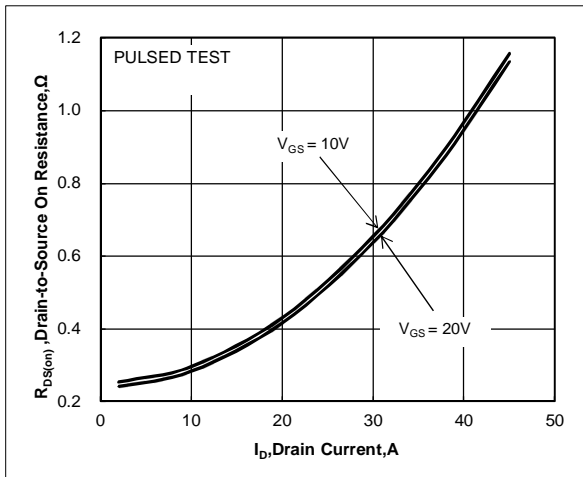


Figure 3. Drain-to-Source On Resistance vs. Drain Current and Gate Voltage

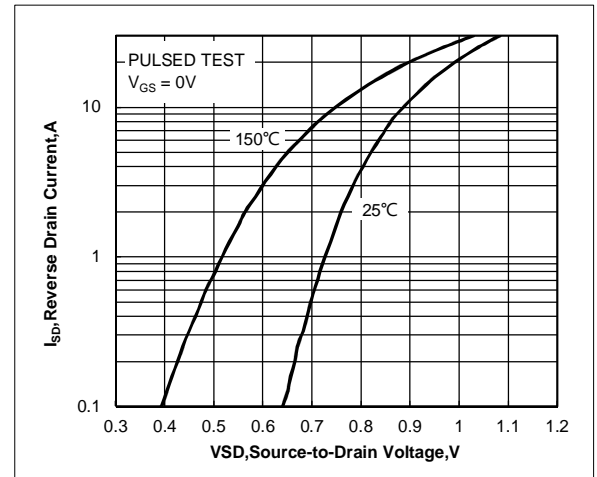


Figure 4. Body Diode Forward Voltage vs. Source Current and Temperature

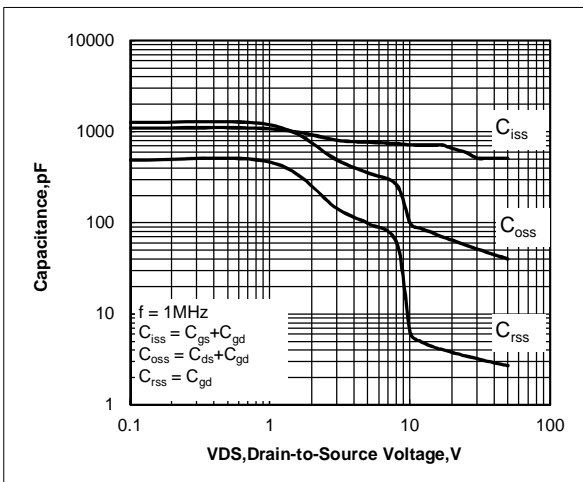


Figure 5. Capacitance Characteristics

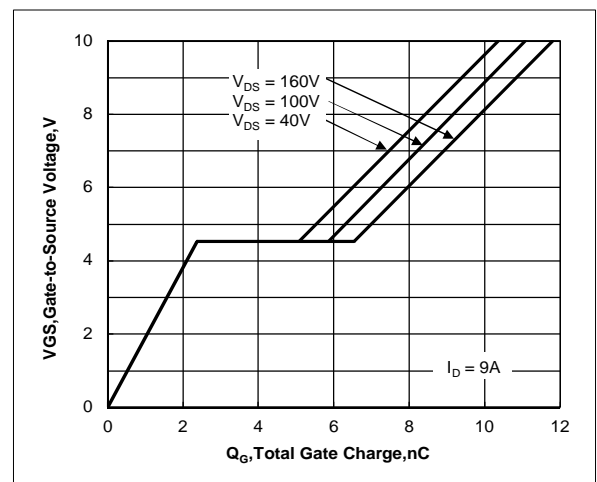


Figure 6. Gate Charge Characteristics

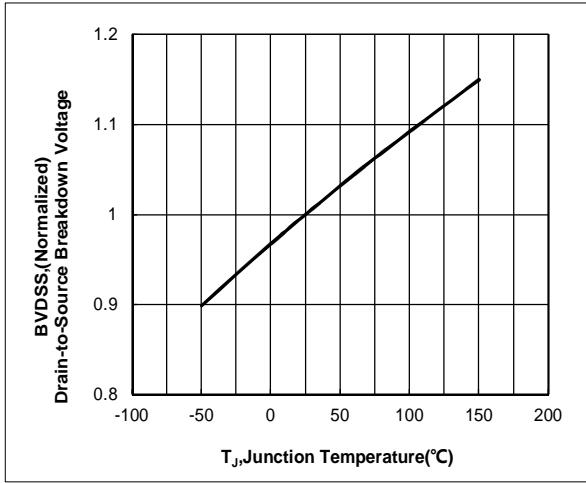


Figure 7. Normalized Breakdown Voltage vs. Junction Temperature

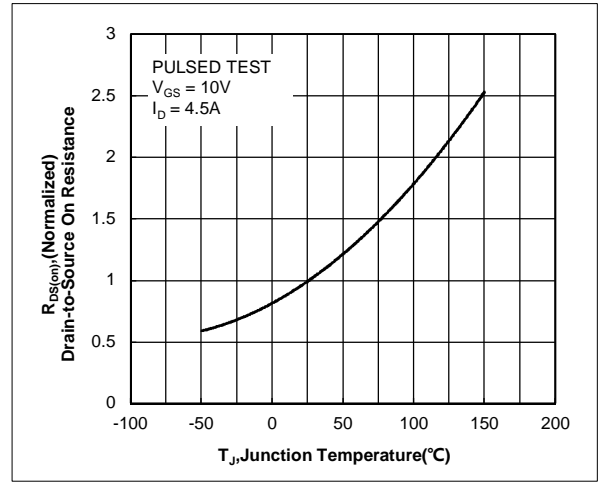


Figure 8. Normalized On Resistance vs. Junction Temperature

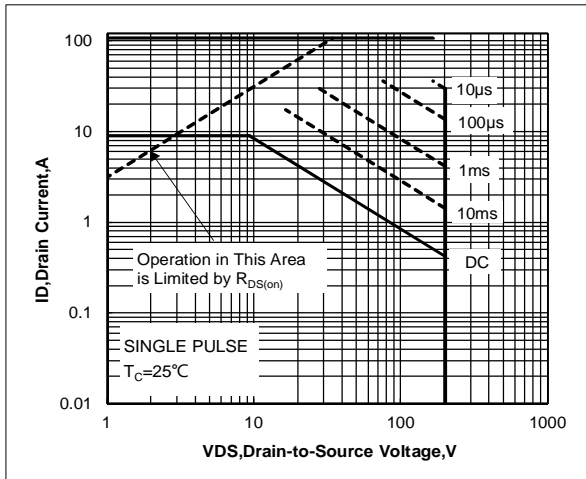


Figure 9. Maximum Safe Operating Area for IRFR220N

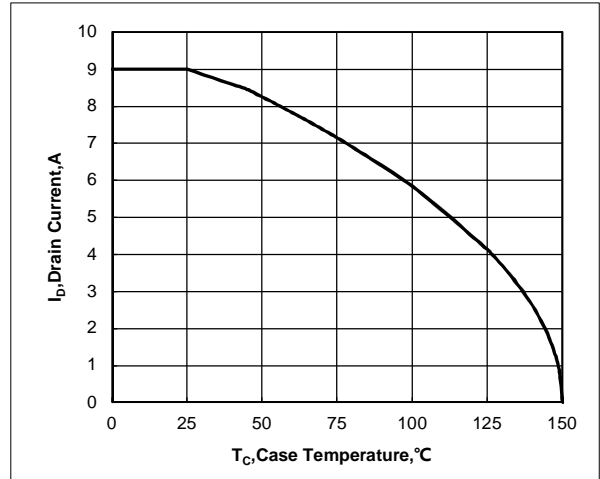


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

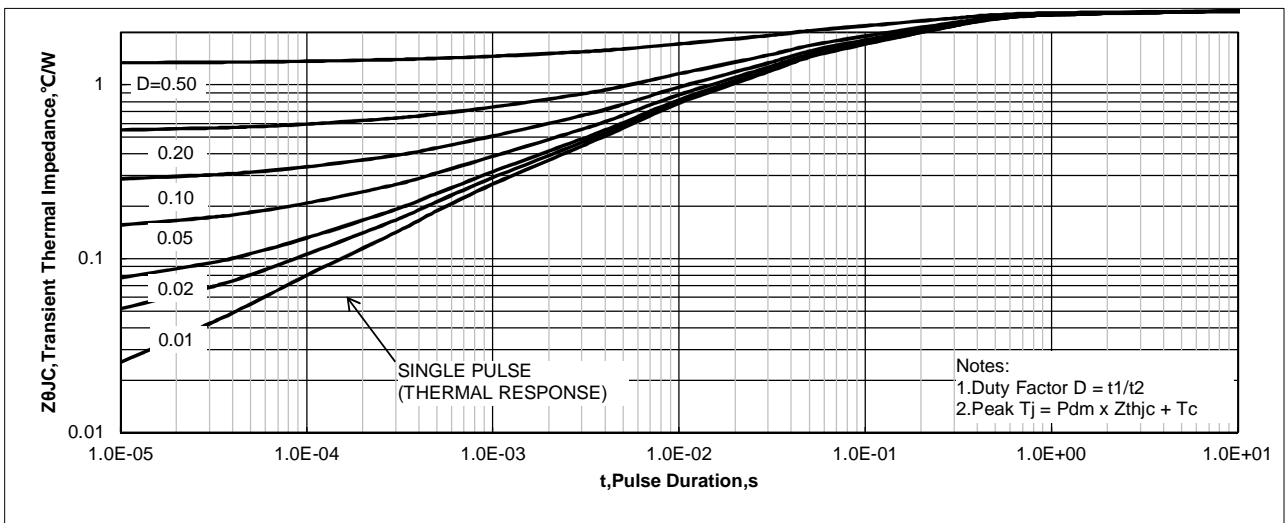


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case for IRFR220N